W255

## 200 MHz 24-Output Buffer for 4 DDR or 3 SDRAM DIMMS

## Features

- One input to 24 output buffer/driver
- Supports up to 4 DDR DIMMs or 3 SDRAM DIMMS
- One additional output for feedback
- SMBus interface for individual output control
- Low skew outputs (< 100 ps)
- Supports 266-, 333-, and 400 MHz DDR SDRAM
- Dedicated pin for power management support
- Space-saving 48-pin SSOP package


## Functional Description

The W 255 is a $3.3 \mathrm{~V} / 2.5 \mathrm{~V}$ buffer designed to distribute high-speed clocks in PC applications. The part has 24 outputs Designers can configure these outputs to support four unbuffered DDR DIMMS or to support three unbuffered standard SDRAM DIMMs and two DDR DIMMS. The W255 can be used in conjunction with the W250 or similar clock synthesizer for the VIA Pro 266 chipset.

The W255 also includes an SMBus interface which can enable or disable each output clock. On power-up, all output clocks are enabled (internal pull up).


## Pin Summary

| Pin Name | Pins | Pin Description |
| :---: | :---: | :---: |
| SEL_DDR | 48 | Input to configure for DDR-ONLY mode or STANDARD SDRAM mode. <br> 1 = DDR-ONLY mode. <br> $0=$ STANDARD SDRAM mode. <br> When SEL_DDR is pulled HIGH or configured for DDR-ONLY mode, pin $4,5,6,7,10,11,15,16,19,20,21,22,27,28,29,30,33,34,38,39$, $42,43,44$ and 45 will be configured as DDR outputs. <br> Connect VDD3.3_2.5 to a 2.5 V power supply in DDR-ONLY mode. <br> When SEL_DDR is pulled LOW or configured for STANDARD SDRAM output, pin 4, 5, 6, 7, 10, 11, 15, 16, 19 and 20, 21,22 will be configured as STANDARD SDRAM outputs.Pin 27, 28, 29, 30, 33, 34, 38, 39, 42, 43,44 and 45 will be configured as DDR outputs. <br> Connect VDD3.3_2.5 to a 3.3V power supply in STANDARD SDRAM mode. |
| SCLK | 25 | SMBus clock input |
| SDATA | 24 | SMBus data input |
| BUF_IN | 13 | Reference input from chipset. 2.5V input for DDR-ONLY mode; 3.3V input for STANDARD SDRAM mode. |
| FBOUT | 1 | Feedback clock for chipset. Output voltage depends on VDD3.3_2.5V. |
| PWR_DWN\# | 36 | Active LOW input to enable power-down mode; all outputs will be pulled LOW. |
| DDR[6:11]T | 28, 30, 34, 39, 43, 45 | Clock outputs. These outputs provide copies of BUF_IN. |
| DDR[6:11]C | 27, 29, 33, 38, 42, 44 | Clock outputs. These outputs provide complementary copies of BUF_IN. |
| $\begin{aligned} & \text { DDR[0:5]T_SDRAM } \\ & {[10,0,2,4,6,8]} \end{aligned}$ | 4, 6, 10, 15, 19, 21 | Clock outputs. These outputs provide copies of BUF_IN. Voltage swing depends on VDD3.3_2.5 power supply. |
| $\begin{aligned} & \text { DDR[0:5]C_SDRAM } \\ & {[11,1,3,5,7,9]} \end{aligned}$ | 5, 7, 11, 16, 20, 22 | Clock outputs. These outputs provide complementary copies of BUF_IN when SEL_DDR is active. These outputs provide copies of BUF_IN when SEL_DDR is inactive. Voltage swing depends on VDD $\overline{3}$.3_2.5 power supply. |
| VDD3.3_2.5 | $2,8,12,17,23$ | Connect to 2.5 V power supply when W255 is configured for DDR-ONLY mode. Connect to 3.3V power supply, when W255 is configured for standard SDRAM mode. |
| VDD2.5 | 32, 37, 41, 47 | 2.5 V voltage supply |
| GND | 3, 9, 14, 18, 26, 31, 35, 40, 46 | Ground |

## Serial Configuration Map

- The serial bits will be read by the clock driver in the following order:

Byte 0 - Bits 7, 6, 5, 4, 3, 2, 1, 0
Byte 1 - Bits 7, 6, 5, 4, 3, 2, 1, 0

Byte N-Bits 7, 6, 5, 4, 3, 2, 1, 0

- Reserved and unused bits should be programmed to "0."
- SMBus Address for the W255 is:

Table 1.

| A6 | A5 | A4 | A3 | A2 | A1 | A0 | R/W |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 1 | 1 | 0 | 1 | 0 | 0 | 1 | ---- |

Byte 6: Outputs Active/Inactive Register ( 1 = Active, $0=$ Inactive), Default = Active

| Bit | Pin \# | Description | Default |
| :---: | :--- | :--- | :--- |
| Bit 7 | - | Reserved, drive to 0 | 0 |
| Bit 6 | - | Reserved, drive to 0 | 0 |
| Bit 5 | - | Reserved, drive to 0 | 0 |
| Bit 4 | 1 | FBOUT | 1 |
| Bit 3 | 45,44 | DDR11T, DDR11C | 1 |
| Bit 2 | 43,42 | DDR10T, DDR10C | 1 |
| Bit 1 | 39,38 | DDR9T, DDR9C | 1 |
| Bit 0 | 34,33 | DDR8T, DDR8C | 1 |

Byte 7: Outputs Active/Inactive Register (1 = Active, 0 = Inactive), Default = Active

| Bit | Pin \# | Description | Default |
| :---: | :--- | :--- | :--- |
| Bit 7 | 30,29 | DDR7T, DDR7C | 1 |
| Bit 6 | 28,27 | DDR6T, DDR6C | 1 |
| Bit 5 | 21,22 | DDR5T_SDRAM8, <br> DDR5C_SDRAM9 | 1 |
| Bit 4 | 19,20 | DDR4T_SDRAM6, <br> DDR4C_SDRAM7 | 1 |
| Bit 3 | 15,16 | DDR3T_SDRAM4, <br> DDR3C_SDRAM5 | 1 |
| Bit 2 | 10,11 | DDR2T_SDRAM2, <br> DDR2C_SDRAM3 | 1 |
| Bit 1 | 6,7 | DDR1T_SDRAM0, <br> DDR1C_SDRAM1 | 1 |
| Bit 0 | 4,5 | DDR0T_SDRAM10, <br> DDR0C_SDRAM11 | 1 |

W255
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## Maximum Ratings

Supply Voltage to Ground Potential ...... -0.5 to +7.0 V
DC Input Voltage (except BUF_IN)............ -0.5 V to $\mathrm{V}_{\mathrm{DD}}+0.5$

Storage Temperature.
Static Discharge Voltage $-65^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$
(per MIL-STD-883, Method 3015)

Operating Conditions ${ }^{[2]}$

| Parameter | Description | Min. | Typ. | Max. | Unit |
| :--- | :--- | :---: | :---: | :---: | :---: |
| VDD3.3 | Supply Voltage | 3.135 |  | 3.465 | V |
| VDD2.5 | Supply Voltage | 2.375 |  | 2.625 | V |
| $\mathrm{~T}_{\mathrm{A}}$ | Operating Temperature (Ambient Temperature) | 0 |  | 70 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{C}_{\text {OUT }}$ | Output Capacitance |  | 6 |  | pF |
| $\mathrm{C}_{\text {IN }}$ | Input Capacitance |  | 5 |  | pF |

Electrical Characteristics Over the Operating Range

| Parameter | Description | Test Conditions | Min. | Typ. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {IL }}$ | Input LOW Voltage | For all pins except SMBus |  |  | 0.8 | V |
| $\mathrm{V}_{\mathrm{IH}}$ | Input HIGH Voltage |  | 2.0 |  |  | V |
| $\mathrm{I}_{\text {IL }}$ | Input LOW Current | $\mathrm{V}_{\text {IN }}=0 \mathrm{~V}$ |  |  | 50 | $\mu \mathrm{A}$ |
| $\mathrm{I}_{\mathrm{IH}}$ | Input HIGH Current | $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\text {DD }}$ |  |  | 50 | $\mu \mathrm{A}$ |
| ${ }^{\mathrm{OH}}$ | Output HIGH Current | $\begin{aligned} & \mathrm{V}_{\mathrm{DD}}=2.375 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{OUT}}=1 \mathrm{~V} \end{aligned}$ | -18 | -32 |  | mA |
| ${ }^{\text {IOL }}$ | Output LOW Current | $\begin{aligned} & \mathrm{V}_{\mathrm{DD}}=2.375 \mathrm{~V} \\ & \mathrm{~V}_{\text {OUT }}=1.2 \mathrm{~V} \end{aligned}$ | 26 | 35 |  | mA |
| $\mathrm{V}_{\mathrm{OL}}$ | Output LOW Voltage ${ }^{[3]}$ | $\mathrm{l}_{\mathrm{OL}}=12 \mathrm{~mA}, \mathrm{~V}_{\mathrm{DD}}=2.375 \mathrm{~V}$ |  |  | 0.6 | V |
| $\mathrm{V}_{\mathrm{OH}}$ | Output HIGH Voltage ${ }^{[3]}$ | $\mathrm{I}_{\mathrm{OH}}=-12 \mathrm{~mA}, \mathrm{~V}_{\mathrm{DD}}=2.375 \mathrm{~V}$ | 1.7 |  |  | V |
| ${ }^{\text {DD }}$ | Supply Current ${ }^{[3]}$ (DDR-only mode) | Unloaded outputs, 133 MHz |  |  | 400 | mA |
| $\mathrm{I}_{\mathrm{DD}}$ | Supply Current (DDR-only mode) | Loaded outputs, 133 MHz |  |  | 500 | mA |
| IDDS | Supply Current | PWR_DWN\# = 0 |  |  | 100 | $\mu \mathrm{A}$ |
| V OUT | Output Voltage Swing | See test circuity (refer to Figure 1) | 0.7 |  | $\mathrm{V}_{\mathrm{DD}}+0.6$ | V |
| $\mathrm{V}_{\mathrm{OC}}$ | Output Crossing Voltage |  | $\begin{gathered} \left(\mathrm{V}_{\mathrm{DD}} / 2\right)- \\ 0.1 \end{gathered}$ | $\mathrm{V}_{\mathrm{DD}} / 2$ | $\begin{gathered} \left(\mathrm{V}_{\mathrm{DD}} / 2\right)+ \\ 0.1 \end{gathered}$ | V |
| $\mathrm{IN}_{\mathrm{DC}}$ | Input Clock Duty Cycle |  | 48 |  | 52 | \% |

Switching Characteristics ${ }^{[4]}$

| Parameter | Name | Test Conditions | Min. | Typ. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| - | Operating Frequency |  | 66 |  | 200 | MHz |
| - | Duty Cycle ${ }^{[3,5]}=\mathrm{t}_{2} \div \mathrm{t}_{1}$ | Measured at 1.4 V for 3.3 V outputs Measured at $\mathrm{V}_{\mathrm{DD}} / 2$ for 2.5 V outputs | $\begin{gathered} \mathrm{IN}_{\mathrm{DC}}- \\ 5 \% \end{gathered}$ |  | $\begin{gathered} \mathrm{IN}_{\mathrm{DC}}+ \\ 5 \% \end{gathered}$ | \% |
| $\mathrm{t}_{3}$ | SDRAM Rising Edge Rate ${ }^{[3]}$ | Measured between 0.4 V and 2.4 V | 1.0 |  | 2.75 | V/ns |
| $\mathrm{t}_{4}$ | SDRAM Falling Edge Rate ${ }^{[3]}$ | Measured between 2.4 V and 0.4 V | 1.0 |  | 2.75 | V/ns |
| $\mathrm{t}_{3 \mathrm{~d}}$ | DDR Rising Edge Rate ${ }^{[3]}$ | Measured between 20\% to 80\% of output (refer to Figure 1) | 0.5 |  | 1.50 | V/ns |

[^0]Switching Characteristics (continued) ${ }^{[4]}$

| Parameter | Name | Test Conditions | Min. | Typ. | Max. | Unit |
| :--- | :--- | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{4 \mathrm{~d}}$ | DDR Falling Edge Rate ${ }^{[3]}$ | Measured between 20\% to 80\% of <br> output (refer to Figure 1) | 0.5 |  | 1.50 | $\mathrm{~V} / \mathrm{ns}$ |
| $\mathrm{t}_{5}$ | Output to Output Skew for DDR ${ }^{[3]}$ | All outputs equally loaded |  |  | 100 | ps |
| $\mathrm{t}_{6}$ | Output to Output Skew for <br> SDRAM $^{[3]}$ | All outputs equally loaded |  |  | 150 | ps |
| $\mathrm{t}_{7}$ | SDRAM Buffer LH Prop. Delay $^{[3]}$ | Input edge greater than 1 V/ns | 5 |  | 10 | ns |
| $\mathrm{t}_{8}$ | SDRAM Buffer HL Prop. Delay ${ }^{[3]}$ | Input edge greater than 1 V/ns | 5 |  | 10 | ns |

## Switching Waveforms

## Duty Cycle Timing



## All Outputs Rise/Fall Time

OUTPUT


Output-Output Skew


SDRAM Buffer HH and LL Propagation Delay


Figure 1 shows the differential clock directly terminated by a $120 \Omega$ resistor.


Figure 1. Differential Signal Using Direct Termination Resistor

## Layout Example for DDR 2.5V Only



FB = Dale ILB1206-300 (300 @ @ 100 MHz ) or TDK ACB 2012L-120
Ceramic Caps C3 $=10-22 \mu \mathrm{~F} \quad \mathrm{C} 4=0.005 \mu \mathrm{~F}$
( $=$ VIA to GND plane layer $\quad$ V = VIA to respective supply plane layer
Note: Each supply plane or strip should have a ferrite bead and capacitors All bypass caps $=0.1 \mu \mathrm{~F}$ ceramic


FB = Dale ILB1206-300 (300 @ 100 MHz ) or TDK ACB 2012L-120
Ceramic Caps C1 and C3 $=10-22 \mu \mathrm{FC} 2$ \& C4 $=0.005 \mu \mathrm{~F} \mathbf{C 6}=0.1 \mu \mathrm{~F}$ ( = VIA to GND plane layer $\quad(\mathrm{V}=$ VIA to respective supply plane layer Note: Each supply plane or strip should have a ferrite bead and capacitors All bypass caps $=0.1 \mu \mathrm{~F}$ ceramic

W255

Ordering Information

| Ordering Code | Package Type | Operating Range |
| :--- | :--- | :--- |
| W255H | $48-$ pin SSOP | Commercial |
| W255HT | $48-$ pin SSOP-Tape and Reel Option | Commercial |
| Lead-free |  |  |
| CYW255OXC | $48-p i n ~ S S O P ~$ | Commercial |
| CYW255OXCT | $48-p i n ~ S S O P-T a p e ~ a n d ~ R e e l ~ O p t i o n ~$ | Commercial |

## Package Drawing and Dimensions

48-lead Shrunk Small Outline Package 048



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[^0]:    Notes:
    2. Multiple Supplies: The voltage on any input or I/O pin cannot exceed the power pin during power-up. Power supply sequencing is NOT required.
    3. Parameter is guaranteed by design and characterization. Not $100 \%$ tested in production.
    4. All parameters specified with loaded outputs.
    5. Duty cycle of input clock is $50 \%$. Rising and falling edge rate is greater than $1 \mathrm{~V} / \mathrm{ns}$.

